Discrete POWER & Signal **Technologies**

MPSA18

FAIRCHILD SEMICONDUCTOR TM

MPSA18



NPN General Purpose Amplifier

This device is designed for low noise, high gain, applications at collector currents from 1 μ A to 50 mA. Sourced from Process 07. See 2N5088 for characteristics.

Absolute Maximum Ratings* TA = 25°C unless otherwise noted

Symbol	Parameter	Value	Units
V_{CEO}	Collector-Emitter Voltage	45	V
V _{CBO}	Collector-Base Voltage	45	V
V_{EBO}	Emitter-Base Voltage	6.5	V
I _C	Collector Current - Continuous	100	mA
T _J , T _{stg}	Operating and Storage Junction Temperature Range	-55 to +150	°C

*These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

NOTES:

1) These ratings are based on a maximum junction temperature of 150 degrees C.
2) These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

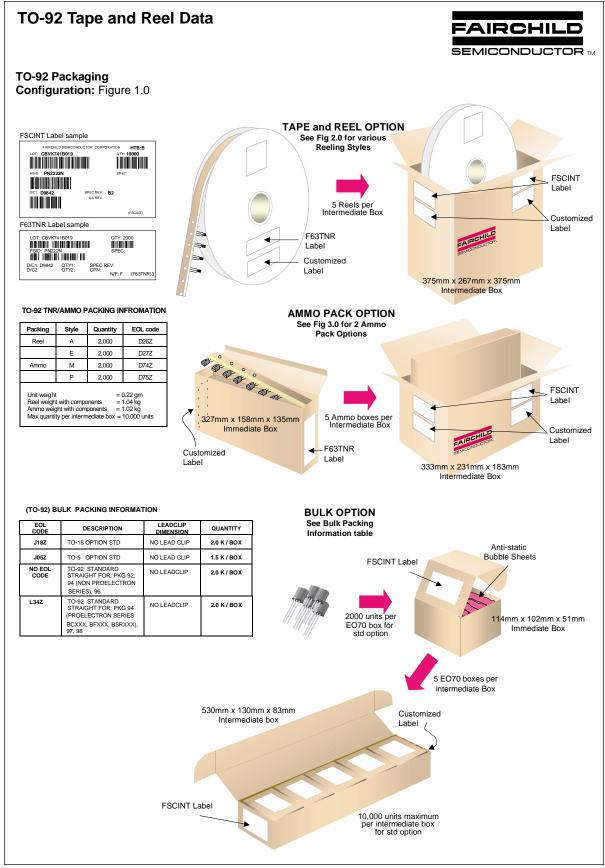
Thermal Characteristics

Thermal Characteristics TA = 25°C unless otherwise noted					
Symbol	Characteristic	Мах	Units		
		MPSA18			
P _D	Total Device Dissipation	625	mW		
	Derate above 25°C	5.0	mW/°C		
$R_{\theta_{JC}}$	Thermal Resistance, Junction to Case	83.3	°C/W		
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	200	°C/W		

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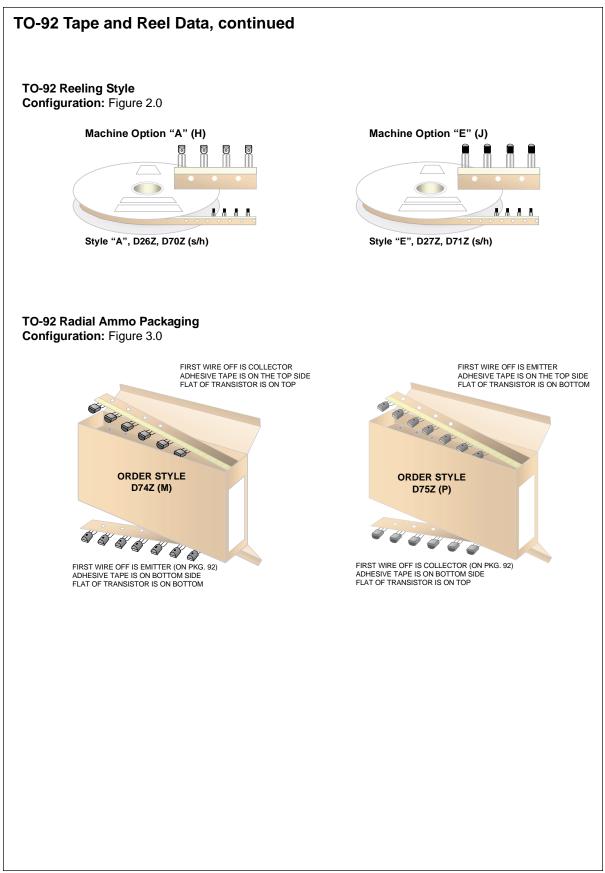
NPN General Purpose Amplifier (continued)

Symbol	Parameter	Test Conditions	Min	Max	Units
					-
	RACTERISTICS	1	1		
(BR)CEO	Collector-Emitter Breakdown Voltage*	$I_{\rm C} = 10 \text{ mA}, I_{\rm B} = 0$	45		V
(BR)CBO	Collector-Base Breakdown Voltage	$I_{C} = 100 \ \mu A, I_{E} = 0$	45		V
(BR)EBO	Emitter-Base Breakdown Voltage	$I_{\rm E} = 10\mu{\rm A}, I_{\rm C} = 0$	6.5		V
СВО	Collector Cutoff Current	$V_{CB} = 30 \text{ V}, I_E = 0$		50	nA
ON CHAF	RACTERISTICS*				
n _{FE}	DC Current Gain	$V_{CE} = 5.0 \text{ V}, I_{C} = 10 \mu\text{A}$	400		
		$V_{CE} = 5.0 \text{ V}, I_{C} = 100 \mu\text{A}$	500		
		$V_{CE} = 5.0 \text{ V}, I_C = 1.0 \text{ mA}$ $V_{CE} = 5.0 \text{ V}, I_C = 10 \text{ mA}$	500 500	1500	
V _{CE(sat)}	Collector-Emitter Saturation Voltage	$I_{\rm C} = 10 \text{ mA}, I_{\rm B} = 0.5 \text{ mA}$	500	0.2	V
		$I_{\rm C} = 50 \text{ mA}, I_{\rm B} = 5.0 \text{ mA}$		0.3	V
V _{BE(ON)}	Base-Emitter On Voltage	$V_{CE} = 5.0 \text{ V}, I_{C} = 1.0 \text{ mA}$		0.7	V
C _{cb}	Collector-Base Capacitance	$V_{CB} = 5.0 \text{ V}, \text{ f} = 1.0 \text{ MHz}$		3.0	pF
C _{eb}	Emitter-Base Capacitance	$V_{EB} = 0.5 V, f = 1.0 MHz$		6.5	pF
f _T	Current Gain - Bandwidth Product	$I_{C} = 1.0 \text{ mA}, V_{CE} = 5.0 \text{ V}, f = 100 \text{ MHz}$	100		MHz
NF	Noise Figure			1.5	dB
NF	Noise Figure			1.5	d

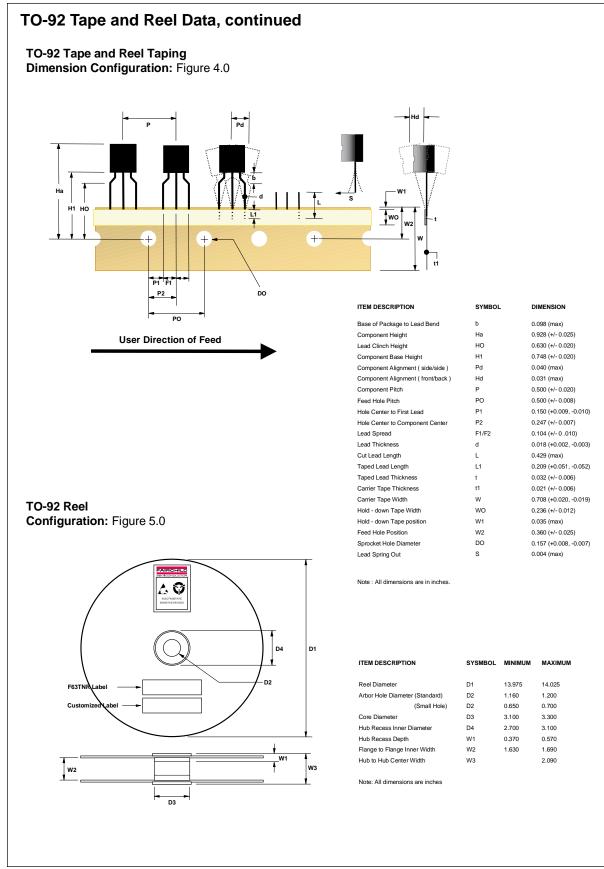


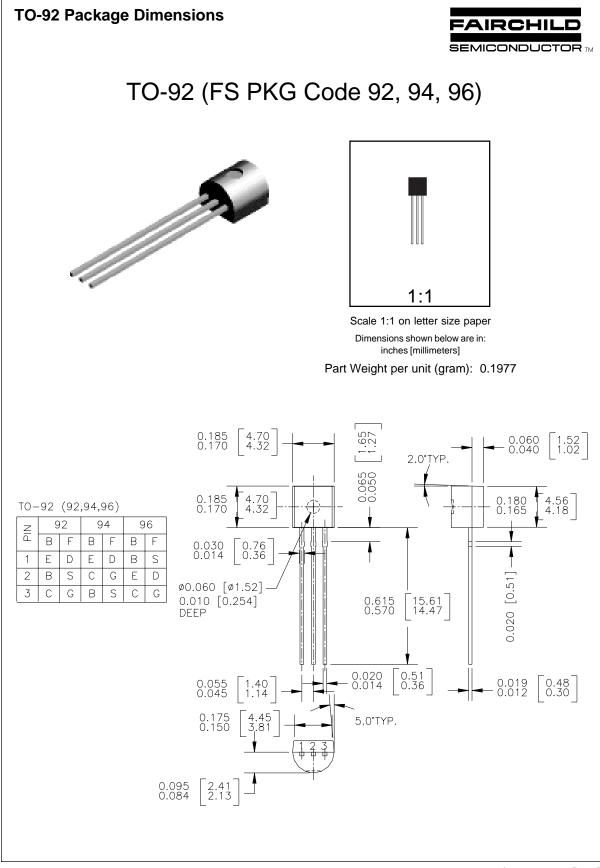
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